

ANEXO

A continuación se presentan los diferentes modelos utilizados para la simulación de la interfaz, así como el programa de cálculo del OTA. En primer lugar se presenta el modelo del acelerómetro torsional, posteriormente el de la capacidad MOS, y por último el programa.

A.1 Modelo de Acelerómetro Torsional

```
-----
--HDL-A model of a pendulum accelerometer                                     --
--                                                                          --
--      ----x1--  /  \  ---- x2 ----                                     --
--      /         /    \  /         \                                     --
--      /         /      \ /         \  ancho                         --
--      /         /        \ /         \                               --
--      /         /          \ /         \                               --
--
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--
-----

ENTITY aceltor IS
  GENERIC (
    ro,      -- Density of the material
    ancho,   -- Is the width of the pendulum
    alto,    -- Is the height of the pendulum
    x2,      -- Is the length of the bigger arm
    x1,      -- Is the length of the smaller arm
    x0,      -- Is half the distance between plates
              -- that are on the pendulum
    dist,    -- Is the distance between the capacitor
              -- plates without any force applied
    k,       -- Is the torsion constant
    psi,     -- Damping factor

    Voffset -- Is the voltage for the minimum
              -- capacitance value
  )

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: analog);

COUPLING (
    alfa,    -- Is the angular position
    cl,      -- Large arm capacitance
    cs,      -- Small arm capacitance
    mvl,     -- Electrostatic torque in the large arm
    mvs      -- Electrostatic torque in the small arm
: analog);

PIN (
    ebl,     -- First node of the large arm capacitor
    ebs,     -- First node of the small arm capacitor
    ecl,     -- Second node of the large arm capacitor
    ecs,     -- Second node of the small arm capacitor
    a        -- Applied acceleration, this could be mechanical.
: electrical);

END ENTITY aceltor;

ARCHITECTURE bhv OF aceltor IS

    STATE ibl, ibs, ico, vbl, vbs, acel: analog;
    CONSTANT ii, b, mg, m0, m1, c0, cl, alfa0, alfa1, e0, c: analog;
    STATE theta, alfa, alfaddt, alfad2dt: analog;
    STATE it, bt: analog;
    STATE thetaddt, thetad2dt: analog;

BEGIN

    RELATION
        PROCEDURAL FOR INIT =>

            ro      := 2.329e3;      --Kg/m3
            ancho   := 1.4e-3;      --m
            alto    := 10.0e-6;     --m
            x2      := 2.0e-3;      --m
            x1      := 1.4e-3;      --m
            x0      := 14.0e-6;     --m
            dist    := 8.7e-6;      --m
            k       := 5.0e-6;      --Nm/rad
            psi     := 102.18;
            Voffset := -0.5;        --V

            e0      := 8.85e-12;    --F/m

            ii      := ro*ancho*alto*(x2**3+x1**3)/3.0;
            b       := 2.0*psi*sqrt(k*ii);
            mg      := ro*ancho*alto*(x2**2-x1**2)/2.0;
            c       := dist/x2;

-- This part linearizes the capacitor and torque equations to avoid
-- a 0/0 singularity.

            alfa1   := c*1.0e-3;
            alfa0   := c*-1.0e-3;
            alfa    := 0.0;
            theta   := 0.0;
--            alfaddt := 0.0;
--            alfad2dt := 0.0;

            c1      := e0*ancho/alfa1*
                    ln((dist+alfa1*x1)/
                    (dist+alfa1*x0));
            m1      := e0*ancho/alfa1**2*
                    (dist*alfa1*(x0-x1)/
                    (dist+alfa1*x0)/(dist+alfa1*x1)+
                    ln((dist+alfa1*x1)/
                    (dist+alfa1*x0)));
            c0      := e0*ancho/alfa0*
                    ln((dist+alfa0*x1)/
                    (dist+alfa0*x0));
            m0      := e0*ancho/alfa0**2*
                    (dist*alfa0*(x0-x1)/

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```

                                (dist+alfa0*x0)/(dist+alfa0*x1)+
                                ln((dist+alfa0*x1)/
                                (dist+alfa0*x0)));

PROCEDURAL FOR AC, DC, TRANSIENT =>

    acel := a.v;

    vbl := [ebl, ecl].v - Voffset;
    vbs := [ebs, ecs].v - Voffset;

    alfa := c*th(theta);
    alfat := alfa;
    alfaddt := ddt(alfat);
    alfad2dt := ddt(alfaddt);
--      thetaddt := ddt(theta);
--      thetad2dt := ddt(thetaddt);

-- We see if we are near to the 0 degrees. In this case we take the linear
-- aproximation

    IF alfa < alfa1 and alfa > alfa0 THEN

        cl := (c1-c0)/(alfa1-alfa0)*
              (alfa-alfa0) + c0;
        mv1 := -(m1-m0)/(alfa1-alfa0)*
              (alfa-alfa0) - m0;

        cs := (c1-c0)/(alfa1-alfa0)*
              (-alfa-alfa0) + c0;
        mvs := (m1-m0)/(alfa1-alfa0)*
              (-alfa-alfa0) + m0;

    ELSE

        cl := e0*ancho/alfa*
              ln((dist+alfa*x1)/
              (dist+alfa*x0));
        mv1 := -e0*ancho/alfa**2*
              (dist*alfa*(x0-x1)/
              (dist+alfa*x0)/(dist+alfa*x1)+
              ln((dist+alfa*x1)/
              (dist+alfa*x0)));

        cs := e0*ancho/-alfa*
              ln((dist-alfa*x1)/
              (dist-alfa*x0));
        mvs := e0*ancho/alfa**2*
              (dist*alfa*(x1-x0)/
              (dist-alfa*x0)/(dist-alfa*x1)+
              ln((dist-alfa*x1)/
              (dist-alfa*x0)));

    END IF;

--We calculate the current for the capacitors.

    ibl := c1*ddt(vbl);
    ibs := cs*ddt(vbs);

    [ebl, ecl].i %= ibl;
    [ebs, ecs].i %= ibs;

--      it := -2.0*c*ii*th(theta)/(ch(theta)**2);
--      bt := c*b/(ch(theta)**2);

EQUATION (theta)
FOR AC, DC, TRANSIENT =>

```

--Equation for the alfa position.

$$ii*alfad2dt + b*alfaddt + k*alfat == \\ mvl*vbl**2 + mvs*vbs**2 + mg*acel;$$

END RELATION;
END ARCHITECTURE bhv;

A.2 Modelo de Capacidad MOS

```

ENTITY capmos IS
  GENERIC(
    area,    -- Area en um^2
    cox,     -- Capacidad del oxido en F
    n,       -- Concentracion de impurezas cm^-3
    vfb,     -- Tension de bandas planas
    mos,     -- Tipo de substrato +1 pmos -1 nmos
    t,       -- Temperatura en K
    :analog
  );

  -- COUPLING(
  --   vs,
  --   chf    -- Capacidad de alta frecuencia
  --   :analog
  -- );

  PIN(
    gate,    -- Port de puerta
    bulk     -- Port de bulk
    :electrical
  );
END ENTITY capmos;

ARCHITECTURE hf OF capmos IS
  constant
    kb,      -- Constante de Boltzman
    q,       -- Carga del electron
    gap,     -- Gap del silicio
    es,      -- Constante dielectrica del silicio
    eox,     -- Constante dielectrica del oxido
    ni,      -- Portadores intrinsecos
    beta,    -- Beta
    ldi,     -- Longitud intrinseca de Debye
    q0,
    c0,
    vf,      -- Potencial de Fermi
    dox,     -- Anchura del oxido
    areacm
    :analog;

  state
    fis,    -- Potencial en la superficie
    vcal,   -- Tension de calculo
    qsc,    -- Cargas en el semiconductor
    v       -- Tension gate-bulk
    :analog;

  variable
    clf,    -- Capacidad de baja frecuencia
    vs,     -- Tension en la superficie
    chf,    -- Capacidad de alta frecuencia
    ccal,   -- Capacidad para calculo
    fir,    -- Potencial se superficie real
    fq,
    fc,
    signvs  -- Signo de vs
    :analog;

BEGIN
  RELATION
    PROCEDURAL FOR INIT =>
      area    := 625.0;      -- um^2
      cox     := 228.0e-9;   -- F/cm^2
      n       := 2.94e16;   -- cm^-3
      vfb     := 0.0;       -- V
      mos     := -1.0;      -- Substrato nmos
      t       := 300.0;     -- K

```

```

kb      := 1.38e-23;
q       := 1.602e-19;
gap     := 1.12;      -- eV
es      := 1.04e-12;
eox     := 3.4e-13;
ni      := 1.0e10;

areacm := area*1.0e-8;

beta    := q/(kb*t);
ldi     := sqrt(es*kb*t/(2.0*q**2*ni));
q0      := 2.0*sqrt(2.0)*q*ni*ldi;
c0      := q0*beta/2.0;
vf      := ln(ni/n);

--          PROCEDURAL FOR DC =>

--          -- Calculo de la capacidad para el caso de DC

--          v := [gate, bulk].v;

--          vs := fis*beta;

--          if vs > 0.0 then signvs := 1.0;
--          elsif vs < 0.0 then signvs := -1.0;
--          else signvs := 0.0;
--          end if;

--          f := sqrt(-vs*sh(vf)-(ch(vf)-ch(vs+vf))) +
--          1.0e-20;

--          qsc := -q0*signvs*f;

--          vcal := fis - qsc/cox;

--          ccal := signvs*es/ldi*(sh(vs+vf)-sh(vf))/
--          (sqrt(2.0)*f);

--          c := cox*ccal/(cox+ccal)*areacm;

--          [gate, bulk].i %= c*ddt(v);

--          PROCEDURAL FOR DC, AC, TRANSIENT =>

--          -- Calculo de la capacidad para el caso de AC

--          v := [gate, bulk].v;

--          fir := fis - vfb;

--          vs := fis*beta;

--          if vs > 0.0 then signvs := 1.0;
--          elsif vs < 0.0 then signvs := -1.0;
--          else signvs := 0.0;
--          end if;

--          fq := sqrt(-vs*sh(vf)-(ch(vf)-ch(vs+vf))) +
--          1.0e-20;

--          qsc := -q0*signvs*fq;

--          vcal := fir - qsc/cox;

--          fc := sqrt(((vs-1.0)*exp(-vf)+
--          exp(-(vs+vf)))/2.0) +
--          1.0e-20;

```

```
--          ccal := signvs*c0*(sh(vs+vf)-sh(vf))/
--          fq;
--
--          clf := ccal/(ccal+cox)*(cox*areacm);
ccal := signvs*c0*exp(-vf)*(1.0-exp(-vs))/
      (2.0*fc);
CHF := ccal/(ccal+cox)*(cox*areacm);
[gate, bulk].i %= CHF*ddt(v);
EQUATION (fis) FOR AC, DC, TRANSIENT =>
-- Nos resuelve la ecuacion de la carga
-- en el semiconductor
v == mos*vcal;
END RELATION;
END ARCHITECTURE hf;
```

A.3 Programa de Cálculo del OTA

```
#include <iostream.h>
#include <math.h>

int main()
{
    double sr, gbw, cl;
    double k1, k3, k5, k7, k9, k11, kib;
    double gm1, ib;
    double vtp = -1, vtn= 0.815;
    double bp = 38e-6, bn = 127.6e-6;
    double v5, v7, vib, vdd=5., vss=0.;

    cout << "Gain Band With: ";
    cin >> gbw;
    cout << "Slew Rate: ";
    cin >> sr;
    cout << "C load: ";
    cin >> cl;

    gm1 = gbw*2*M_PI*cl;
    ib = sr*cl;

    k1 = gm1/2./bp/(0.2);
    k3 = 2.*ib/bn/(0.5*0.5);
    v5 = 2.4-(0.5);
    // k5 = gm1/2./bn/(v5-vtn);
    k5 = 2.*ib/bn/((0.3)*(0.3));
    v7 = -2.4-(-0.5);
    // k7 = gm1/2./bp/(vtp-v7);
    k7 = 2.*ib/bp/((0.3)*(0.3));
    k9 = 2.*ib/bp/(0.5*0.5);
    k11 = 2.*ib/bp/(0.3*0.3);
    vib = (vdd-vss)-(-(-0.3+vtp)+0.5+vtn);
    kib = 2.*ib/bp/(vib*vib);

    cout << "k1 = " << k1 << '\n';
    cout << "k3 = " << k3 << '\n';
    cout << "k5 = " << k5 << '\n';
    cout << "k7 = " << k7 << '\n';
    cout << "k9 = " << k9 << '\n';
    cout << "k11 = " << k11 << '\n';
    cout << "kib = " << kib << '\n';
    cout << "Ib = " << ib << '\n';
}
```